

## 6A High-Speed MOSFET Drivers

#### Features

- Latch-Up Protected: will withstand >1.5A Reverse Output Current
- Logic Input will withstand Negative Swing Up to 5V
- ESD Protected: 4 kV
- Matched Rise and Fall Times:
- 25 nsec (2500 pF load)
- High Peak Output Current: 6A Peak
- Wide Input Supply Voltage Operating Range:
- 4.5V to 18V
- High Capacitive Load Drive Capability: 10,000 pF
- Short Delay Time: 55 nsec (typ.)
- Logic High Input, Any Voltage: 2.4V to V<sub>DD</sub>
- Low Supply Current With Logic '1' Input:
  450 µA (tvp.)
- Low Output Impedance: 2.5Ω
- Output Voltage Swing to Within 25 mV of Ground or  $\rm V_{DD}$

## Applications

- · Switch-Mode Power Supplies
- Motor Controls
- Pulse Transformer Driver
- · Class D Switching Amplifiers

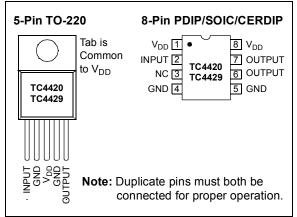
#### **General Description**

The TC4420/TC4429 are 6A (peak), single output MOSFET drivers. The TC4429 is an inverting driver (pin-compatible with the TC429), while the TC4420 is a non-inverting driver. These drivers are fabricated in CMOS for lower power, more efficient operation versus bipolar drivers.

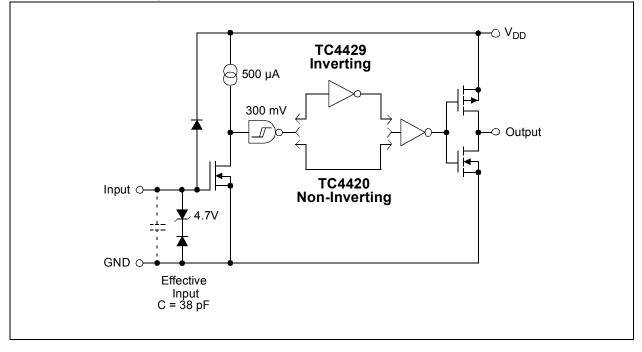
Both devices have TTL-compatible inputs, which can be driven as high as  $V_{DD}$  + 0.3V or as low as -5V without upset or damage to the device. This eliminates the need for external level-shifting circuitry and its associated cost and size. The output swing is rail-to-rail, ensuring better drive voltage margin, especially during power-up/ power-down sequencing. Propagational delay time is only 55 nsec (typ.) and the output rise and fall times are only 25 nsec (typ.) into 2500 pF across the usable power supply range.

Unlike other drivers, the TC4420/TC4429 are virtually latch-up proof. They replace three or more discrete components, saving PCB area, parts and improving overall system reliability.

## Package Types:



## **Functional Block Diagram**



## 1.0 ELECTRICAL CHARACTERISTICS

### Absolute Maximum Ratings†

Supply Voltage	+20V
Input Voltage – 5V	to V <sub>DD</sub> + 0.3V
Input Current (V <sub>IN</sub> > V <sub>DD</sub> )	50 mA
Power Dissipation ( $T_A \le 70^{\circ}C$ )	
PDIP	730 mW
SOIC	470 mW
CERDIP	800 mW
5-Pin TO-220	1.6W
Package Power Dissipation ( $T_A \le 25^{\circ}C$ )	
5-Pin TO-220 (With Heatsink)	12.5W
Derating Factors (To Ambient)	
PDIP	8 mW/°C
SOIC	4 mW/°C
CERDIP	6.4 mW/°C
5-Pin TO-220	12 mW/°C
Thermal Impedances (To Case)	
5-Pin TO-220 R <sub>θJ-C</sub>	10°C/W

† Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

## DC CHARACTERISTICS

<b>Electrical Specifications:</b> Unless otherwise noted, $T_A = +25^{\circ}C$ with 4.5V $\leq V_{DD} \leq 18V$ .									
Parameters	Sym	Min	Тур	Max	Units	Conditions			
Input									
Logic '1', High Input Voltage	V <sub>IH</sub>	2.4	1.8	—	V				
Logic '0', Low Input Voltage	V <sub>IL</sub>	—	1.3	0.8	V				
Input Voltage Range	V <sub>IN</sub>	- 5		V <sub>DD</sub> +0.3	V				
Input Current	I <sub>IN</sub>	-10	_	+10	μA	$0V \le V_{IN} \le V_{DD}$			
Output									
High Output Voltage	V <sub>OH</sub>	V <sub>DD</sub> – 0.025	_	—	V	DC TEST			
Low Output Voltage	V <sub>OL</sub>	—	_	0.025	V	DC TEST			
Output Resistance, High	R <sub>OH</sub>	—	2.1	2.8	Ω	I <sub>OUT</sub> = 10 mA, V <sub>DD</sub> = 18V			
Output Resistance, Low	R <sub>OL</sub>	—	1.5	2.5	Ω	I <sub>OUT</sub> = 10 mA, V <sub>DD</sub> = 18V			
Peak Output Current	I <sub>PK</sub>	—	6.0	—	Α	V <sub>DD</sub> = 18V			
Latch-Up Protection Withstand Reverse Current	I <sub>REV</sub>	_	> 1.5	—	A	Duty cycle $\leq$ 2%, t $\leq$ 300 µsec			
Switching Time (Note 1)									
Rise Time	t <sub>R</sub>	_	25	35	nsec.	<b>Figure 4-1</b> , C <sub>L</sub> = 2,500 pF			
Fall Time	t <sub>F</sub>	_	25	35	nsec.	<b>Figure 4-1</b> , C <sub>L</sub> = 2,500 pF			
Delay Time	t <sub>D1</sub>		55	75	nsec.	Figure 4-1			
Delay Time	t <sub>D2</sub>	_	55	75	nsec.	Figure 4-1			
Power Supply				-	•	•			
Power Supply Current	۱ <sub>S</sub>	_	0.45 55	1.5 150	mΑ μΑ	V <sub>IN</sub> = 3V V <sub>IN</sub> = 0V			
Operating Input Voltage	V <sub>DD</sub>	4.5	—	18	V				

Note 1: Switching times ensured by design.

## DC CHARACTERISTICS (OVER OPERATING TEMPERATURE RANGE)

Parameters	Sym	Min	Тур	Мах	Units	Conditions		
Input				•				
Logic '1', High Input Voltage	V <sub>IH</sub>	2.4		_	V			
Logic '0', Low Input Voltage	V <sub>IL</sub>	_		0.8	V			
Input Voltage Range	V <sub>IN</sub>	- 5		V <sub>DD</sub> + 0.3	V			
Input Current	I <sub>IN</sub>	-10	_	+10	μA	$0V \le V_{IN} \le V_{DD}$		
Output								
High Output Voltage	V <sub>OH</sub>	$V_{DD} - 0.025$	_	—	V	DC TEST		
Low Output Voltage	V <sub>OL</sub>	—	_	0.025	V	DC TEST		
Output Resistance, High	R <sub>OH</sub>	—	3	5	Ω	I <sub>OUT</sub> = 10 mA, V <sub>DD</sub> = 18V		
Output Resistance, Low	R <sub>OL</sub>	—	2.3	5	Ω	I <sub>OUT</sub> = 10 mA, V <sub>DD</sub> = 18V		
Switching Time (Note 1)								
Rise Time	t <sub>R</sub>	—	32	60	nsec.	<b>Figure 4-1</b> , C <sub>L</sub> = 2,500 pF		
Fall Time	t <sub>F</sub>	_	34	60	nsec.	Figure 4-1, C <sub>L</sub> = 2,500 pF		
Delay Time	t <sub>D1</sub>	—	50	100	nsec.	Figure 4-1		
Delay Time	t <sub>D2</sub>	_	65	100	nsec.	Figure 4-1		
Power Supply								
Power Supply Current	۱ <sub>S</sub>	—	0.45	3	mA	V <sub>IN</sub> = 3V		
		—	60	400	μA	V <sub>IN</sub> = 0V		
Operating Input Voltage	$V_{DD}$	4.5	_	18	V			

Note 1: Switching times ensured by design.

## **TEMPERATURE CHARACTERISTICS**

<b>Electrical Specifications:</b> Unless otherwise noted, all parameters apply with $4.5V \le V_{DD} \le 18V$ .								
Sym	Min	Тур	Max	Units	Conditions			
T <sub>A</sub>	0		+70	°C				
T <sub>A</sub>	-25	_	+85	°C				
T <sub>A</sub>	-40		+85	°C				
T <sub>A</sub>	-55	_	+125	°C				
T <sub>A</sub>	-40	_	+125	°C				
TJ	—	_	+150	°C				
T <sub>A</sub>	-65	_	+150	°C				
$\theta_{JA}$		125		°C/W				
$\theta_{JA}$		155		°C/W				
$\theta_{JA}$	_	150		°C/W				
$\theta_{JA}$		71		°C/W				
	$\begin{array}{c c} \textbf{Sym} \\ \hline T_A \\ \hline T_A \\ \hline T_A \\ \hline T_A \\ \hline T_J \\ \hline T_A \\ \hline \theta_{JA} \\ \hline \theta_{JA} \\ \theta_{JA} \\ \end{array}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $			

## 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

**Note:** Unless otherwise indicated,  $T_A = +25^{\circ}C$  with  $4.5V \le V_{DD} \le 18V$ .

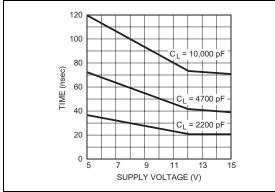
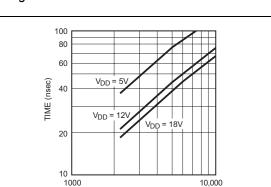


FIGURE 2-1: Rise Time vs. Supply Voltage.



CAPACITIVE LOAD (pF)

FIGURE 2-2: Rise Time vs. Capacitive Load.

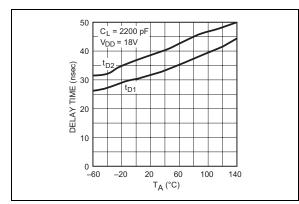


FIGURE 2-3: Temperature.

Propagation Delay Time vs.

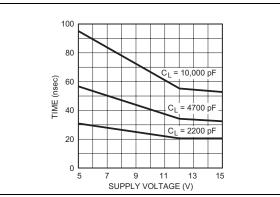


FIGURE 2-4: Voltage.

Fall Time vs. Supply

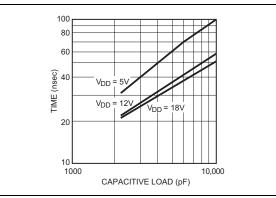


FIGURE 2-5: Fall Time vs. Capacitive Load.

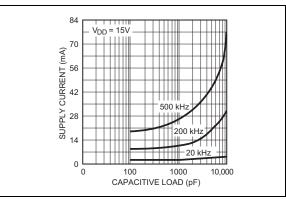
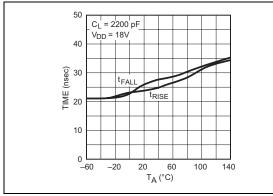


FIGURE 2-6: Capacitive Load.

Supply Current vs.

Note: Unless otherwise indicated, T<sub>A</sub> = +25°C with 4.5V  $\leq$  V<sub>DD</sub>  $\leq$  18V.



**FIGURE 2-7:** Rise and Fall Times vs. Temperature.

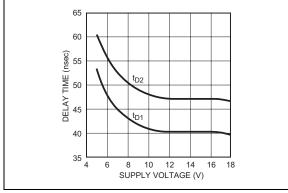


FIGURE 2-8: Propa Supply Voltage.

Propagation Delay Time vs.

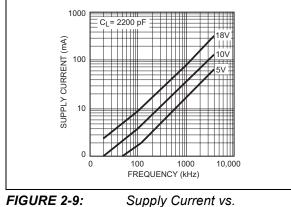


FIGURE 2-9: Frequency.

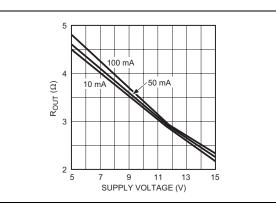
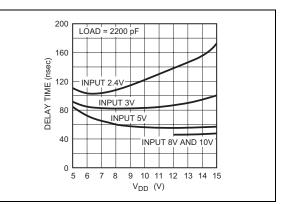


FIGURE 2-10:High-State OutputResistance vs Supply Voltage.



**FIGURE 2-11:** Effect of Input Amplitude on Propagation Delay.

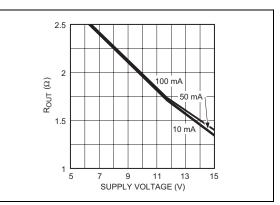


FIGURE 2-12: Low-State Output Resistance vs. Supply Voltage.

Note: Unless otherwise indicated,  $T_A$  = +25°C with 4.5V  $\,\leq V_{DD} \leq$  18V.

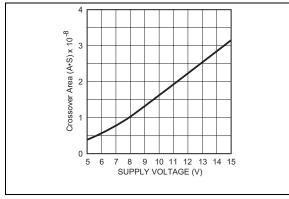


FIGURE 2-13: Crossover Energy \*.

\* The values on this graph represent the loss seen by the driver during one complete cycle. For a single transition, divide the value by 2.

## 3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

#### TABLE 3-1: PIN FUNCTION TABLE

Pin No. (8-Pin PDIP, SOIC, CERDIP)	Pin No. (5-Pin TO-220)	Symbol	Description
1	_	V <sub>DD</sub>	Supply input, 4.5V to 18V
2	1	INPUT	Control input, TTL/CMOS-compatible input
3	—	NC	No Connection
4	2	GND	Ground
5	4	GND	Ground
6	5	OUTPUT	CMOS push-pull output
7	—	OUTPUT	CMOS push-pull output
8	3	V <sub>DD</sub>	Supply input, 4.5V to 18V

### 3.1 Supply Input (V<sub>DD</sub>)

The V<sub>DD</sub> input is the bias supply for the MOSFET driver and is rated for 4.5V to 18V with respect to the ground pins. The V<sub>DD</sub> input should be bypassed to ground with a local ceramic capacitor. The value of the capacitor should be chosen based on the capacitive load that is being driven. A minimum value of 1.0  $\mu$ F is suggested.

#### 3.2 Control Input

The MOSFET driver input is a high-impedance, TTL/CMOS-compatible input. The input circuitry of the TC4420/TC4429 MOSFET driver also has a "speedup" capacitor. This helps to decrease the propagation delay times of the driver. Because of this, input signals with slow rising or falling edges should not be used as this can result in double-pulsing of the MOSFET driver output.

### 3.3 CMOS Push-Pull Output

The MOSFET driver output is a low-impedance, CMOS, push-pull style output, capable of driving a capacitive load with 6.0A peak currents. The MOSFET driver output is capable of withstanding 1.5A peak reverse currents of either polarity.

### 3.4 Ground

The ground pins are the return path for the bias current and for the high peak currents that discharge the load capacitor. The ground pins should be tied into a ground plane or have very short traces to the bias supply source return.

## 4.0 APPLICATIONS INFORMATION

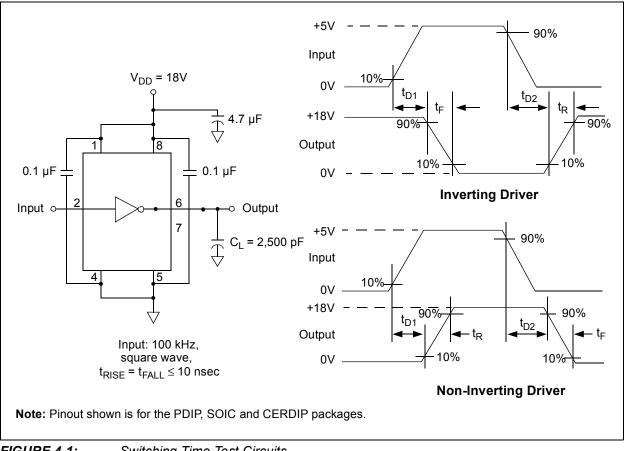
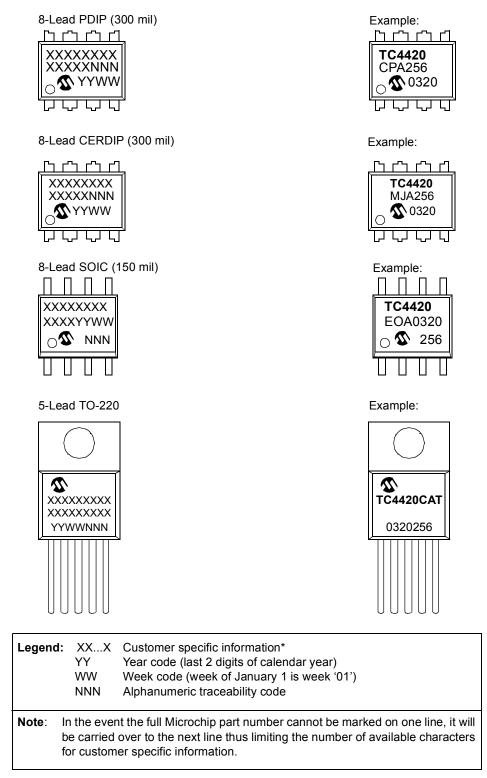


FIGURE 4-1: Switching Time Test Circuits.

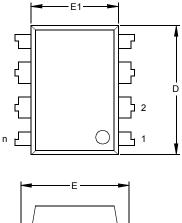
## 5.0 PACKAGING INFORMATION

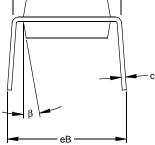
### 5.1 Package Marking Information

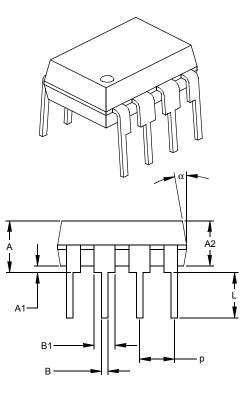


\* Standard OTP marking consists of Microchip part number, year code, week code, and traceability code.

8-Lead Plastic Dual In-line (P) – 300 mil (PDIP)







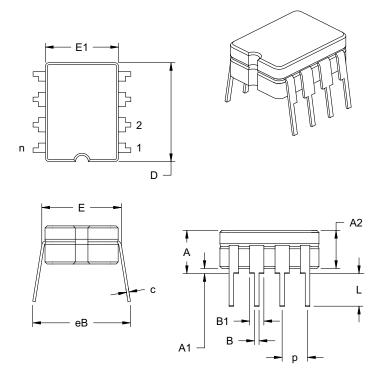
n Limits n p	MIN	NOM 8	MAX	MIN	NOM	MAX
_		0				110 01
р		0			8	
		.100			2.54	
Α	.140	.155	.170	3.56	3.94	4.32
A2	.115	.130	.145	2.92	3.30	3.68
A1	.015			0.38		
E	.300	.313	.325	7.62	7.94	8.26
E1	.240	.250	.260	6.10	6.35	6.60
D	.360	.373	.385	9.14	9.46	9.78
L	.125	.130	.135	3.18	3.30	3.43
С	.008	.012	.015	0.20	0.29	0.38
B1	.045	.058	.070	1.14	1.46	1.78
В	.014	.018	.022	0.36	0.46	0.56
eB	.310	.370	.430	7.87	9.40	10.92
α	5	10	15	5	10	15
β	5	10	15	5	10	15
	A        A2        A1        E        D        L        C        B1        B        eB        α	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $

\* Controlling Parameter § Significant Characteristic

Notes:

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side. JEDEC Equivalent: MS-001 Drawing No. C04-018

## 8-Lead Ceramic Dual In-line – 300 mil (CERDIP)



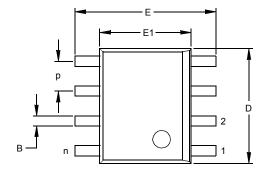
	Units			INCHES*			3
Dimension	Limits	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	р		.100			2.54	
Top to Seating Plane	A	.160	.180	.200	4.06	4.57	5.08
Standoff §	A1	.020	.030	.040	0.51	0.77	1.02
Shoulder to Shoulder Width	E	.290	.305	.320	7.37	7.75	8.13
Ceramic Pkg. Width	E1	.230	.265	.300	5.84	6.73	7.62
Overall Length	D	.370	.385	.400	9.40	9.78	10.16
Tip to Seating Plane	L	.125	.163	.200	3.18	4.13	5.08
Lead Thickness	С	.008	.012	.015	0.20	0.29	0.38
Upper Lead Width	B1	.045	.055	.065	1.14	1.40	1.65
Lower Lead Width	В	.016	.018	.020	0.41	0.46	0.51
Overall Row Spacing	eB	.320	.360	.400	8.13	9.15	10.16

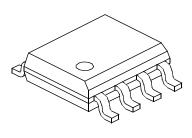
\*Controlling Parameter

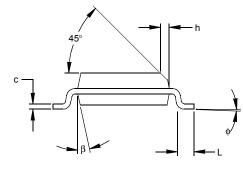
JEDEC Equivalent: MS-030

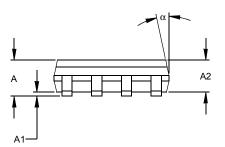
Drawing No. C04-010

### 8-Lead Plastic Small Outline (OA) – Narrow, 150 mil (SOIC)









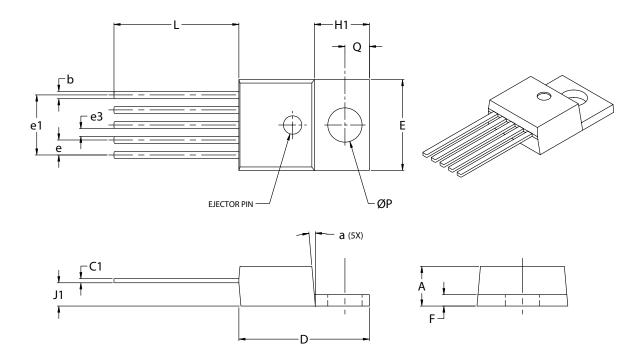
	Units				N	IILLIMETERS	5
Dimensi	on Limits	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	р		.050			1.27	
Overall Height	Α	.053	.061	.069	1.35	1.55	1.75
Molded Package Thickness	A2	.052	.056	.061	1.32	1.42	1.55
Standoff §	A1	.004	.007	.010	0.10	0.18	0.25
Overall Width	E	.228	.237	.244	5.79	6.02	6.20
Molded Package Width	E1	.146	.154	.157	3.71	3.91	3.99
Overall Length	D	.189	.193	.197	4.80	4.90	5.00
Chamfer Distance	h	.010	.015	.020	0.25	0.38	0.51
Foot Length	L	.019	.025	.030	0.48	0.62	0.76
Foot Angle	φ	0	4	8	0	4	8
Lead Thickness	С	.008	.009	.010	0.20	0.23	0.25
Lead Width	В	.013	.017	.020	0.33	0.42	0.51
Mold Draft Angle Top	α	0	12	15	0	12	15
Mold Draft Angle Bottom	β	0	12	15	0	12	15

\* Controlling Parameter § Significant Characteristic

Notes:

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side. JEDEC Equivalent: MS-012 Drawing No. C04-057

### 5-Lead TO-220



	Units			MILLIMETERS		
Dimension Limits		MIN	MAX	MIN	MAX	
Lead Pitch	е	.060	.072	1.52	1.83	
Overall Lead Centers	e1	.263	.273	6.68	6.93	
Space Between Leads	e3	.030	.040	0.76	1.02	
Overall Height	A	.160	.190	4.06	4.83	
Overall Width	E	.385	.415	9.78	10.54	
Overall Length	D	.560	.590	14.22	14.99	
Flag Length	H1	.234	.258	5.94	6.55	
Flag Thickness	F	.045	.055	1.14	1.40	
Through Hole Center	Q	.103	.113	2.62	2.87	
Through Hole Diameter	Р	.146	.156	3.71	3.96	
Lead Length	L	.540	.560	13.72	14.22	
Base to Bottom of Lead	J1	.090	.115	2.29	2.92	
Lead Thickness	C1	.014	.022	0.36	0.56	
Lead Width	b	.025	.040	0.64	1.02	
Mold Draft Angle	а	3°	7°	3°	7°	

\*Controlling Parameter

Notes:

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side. JEDEC equivalent: TO-220

Drawing No. C04-036

## **PRODUCT IDENTIFICATION SYSTEM**

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.	× / <u>×</u> ×	Exa	amples:	
Device	Temperature Package Range	a)	TC4420CAT:	6A High-Speed MOSFET Driver, Non-inverting, TO-220 package, 0°C to +70°C.
Device: Temperature Range:	TC4420: 6A High-Speed MOSFET Driver, Non-Inverting TC4429: 6A High-Speed MOSFET Driver, Inverting C = 0°C to +70°C	b)	TC4420IJA:	6A High-Speed MOSFET Driver, Non-inverting, CERDIP package, -25°C to +85°C.
iemperature Kange.	$ \begin{array}{rcl} I &=& -25^{\circ}C \text{ to } +85^{\circ}C \text{ (CERDIP Only)} \\ I &=& -40^{\circ}C \text{ to } +85^{\circ}C \\ V &=& -40^{\circ}C \text{ to } +125^{\circ}C \\ M &=& -55^{\circ}C \text{ to } +125^{\circ}C \text{ (CERDIP Only)} \end{array} $	C)	TC4420EOA:	6A High-Speed MOSFET Driver, Non-inverting, SOIC package, -40°C to +85°C.
Package:	AT = TO-220, 5-lead JA = Ceramic Dual In-line (300 mil Body), 8-lead PA = Plastic DIP (300 mil Body), 8-lead	d)	TC4420VAT:	6A High-Speed MOSFET Driver, Non-inverting, TO-220 package, -40°C to +125°C.
	OA = Plastic SOIC, (150 mil Body), 8-lead OA713 = Plastic SOIC, (150 mil Body), 8-lead Tape and Reel	e)	TC4420MJA:	6A High-Speed MOSFET Driver, Non-inverting, CERDIP package, -55°C to +125°C
		a)	TC4429CAT:	A High-Speed MOSFET Driver, Inverting, TO-220 package, 0°C to +70°C
		b)	TC4429IJA:	A High-Speed MOSFET Driver, Inverting, CERDIP package, -25°C to +85°C
		c)	TC4429EPA:	A High-Speed MOSFET Driver, Inverting, PDIP package, -40°C to +85°C
		d)	TC4429VAT:	A High-Speed MOSFET Driver, Inverting, TO-220 package, -40°C to +125°C
		e)	TC4429MJA:	A High-Speed MOSFET Driver, Inverting, CERDIP package, -55°C to +125°C

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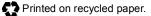
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